

PLEASE AMEND THE CLAIMS AS FOLLOWS:

19. (TWICE AMENDED) A cylindrical shaped, capacitor structure,
featuring a cylindrical storage node structure comprised
of an underlying, uniformly doped, cylindrical
polysilicon shape and an overlying agglomerated metal
5 silicide layer, comprising:

 said cylindrical polysilicon shape comprised of a
bottom polysilicon shape located on a first section of a
top surface of an underlying planar, insulator layer, with
said bottom polysilicon shape overlying and contacting a
10 top surface of a plug structure which in turn is located
in an opening in said insulator layer, and with said
cylindrical polysilicon shape comprised of uniformly
doped, vertical polysilicon shapes, located overlying
second sections of said planar, insulator layer, with
15 bottom portions of said vertical polysilicon shapes
butting edges of said bottom polysilicon shape;

5 said agglomerated metal silicide layer, with a
roughened top surface, located on exposed portions of said
cylindrical polysilicon shape, featuring agglomerated
metal silicide on top surface of said bottom polysilicon
shape, and on all surfaces of uniformly doped, said
vertical polysilicon shapes, resulting in said
cylindrical shape storage node structure comprised of
said agglomerated metal silicide layer on said
cylindrical polysilicon shape;

10 a capacitor dielectric layer located on the
exposed surfaces of said cylindrical shape storage node
structure; and

 an upper electrode, covering said capacitor
dielectric layer.
